

Form PTO-1449				ATTY. DOCKET NO. 3430-0199P		APPLICATION NO. NEW		
INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)				APPLICANT Jae-Gab LEE et al.				
				FILING DATE January 14, 2004		GROUP Unassigned		
U.S. PATENT DOCUMENTS								
EXAMINER INITIAL	DOCUMENT NUMBER	Kind	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
ML	US 5,959,358	A	1999-09-28	Lanford et al.	—	—	—	
ML	US 6,037,257	A	2000-03-14	Chiang et al.	—	—	—	
ML	US 6,165,917	A	2000-12-26	Batey et al.	—	—	—	
ML	US 6,249,055	B1	2001-06-19	Dubin	—	—	—	
ML	US 2001/0034126	A1	2001-10-25	Ding et al.	—	—	—	
	US							
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FOREIGN PATENT DOCUMENTS								
Office	DOCUMENT NUMBER	Kind	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION	
							YES	NO
OTHER DOCUMENTS (Include Name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.)								
ML	Landford et al., "Low-Temperature Passivation of Copper by Doping with Al or Mg," Thin Solid Films, 262 (1995) 234-241.							
ML	Ding et al., "Thermal Annealing of Buried Al Barrier Layers to Passivate the Surface of Copper Films," Appl. Phys. Lett., 65 (1994) 1778							
ML	Sirringhaus et al., "Self-Passivated Copper Gates for Amorphous Silicon Thin-Film Transistors," IEEE Elec. Dev. Lett., Vol. 18, No. 8 (Aug. 1997) 388.							
ML	Itow et al., "Self-Aligned Passivation on Copper Interconnection Durability Against Oxidizing Ambient Annealing," Appl. Phys. Lett., 63 (1993) 934.							
EXAMINER ML				DATE CONSIDERED 4/25/04				
EXAMINER: Initial if citation considered, whether or not citation is in conformance with M.P.S.P. 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								

